

A cross-sectional view of a semiconductor device 100. The device consists of a substrate 102 with a top layer 106. A patterned layer 104 is on the substrate, with openings 103. A layer 118 is on top of 104, with openings 120. A layer 122 is on top of 118, with openings 122. A layer 108 is on top of 122, with openings 108. A layer 116 is on top of 108.

Fig. 1B

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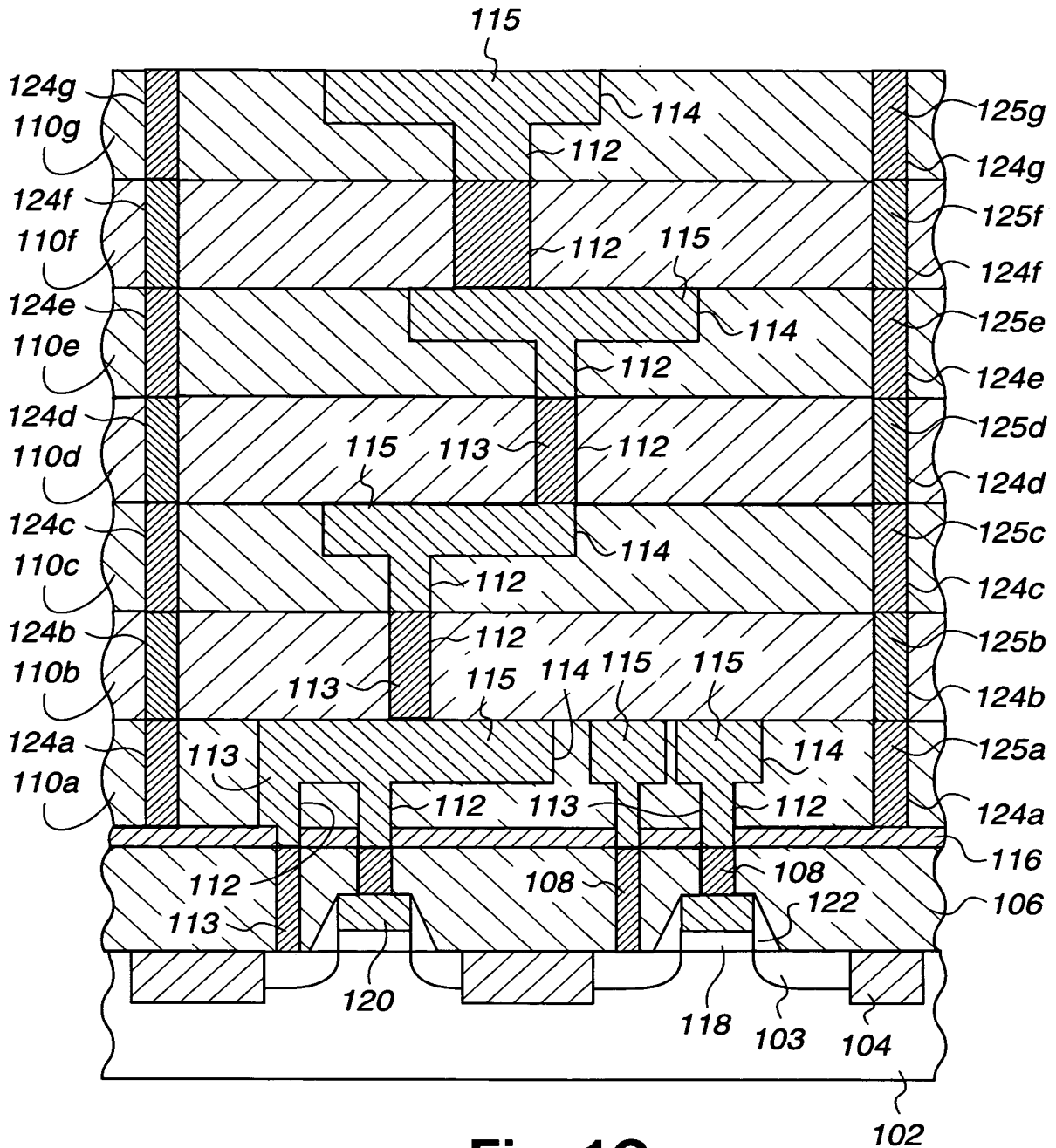


Fig. 1C

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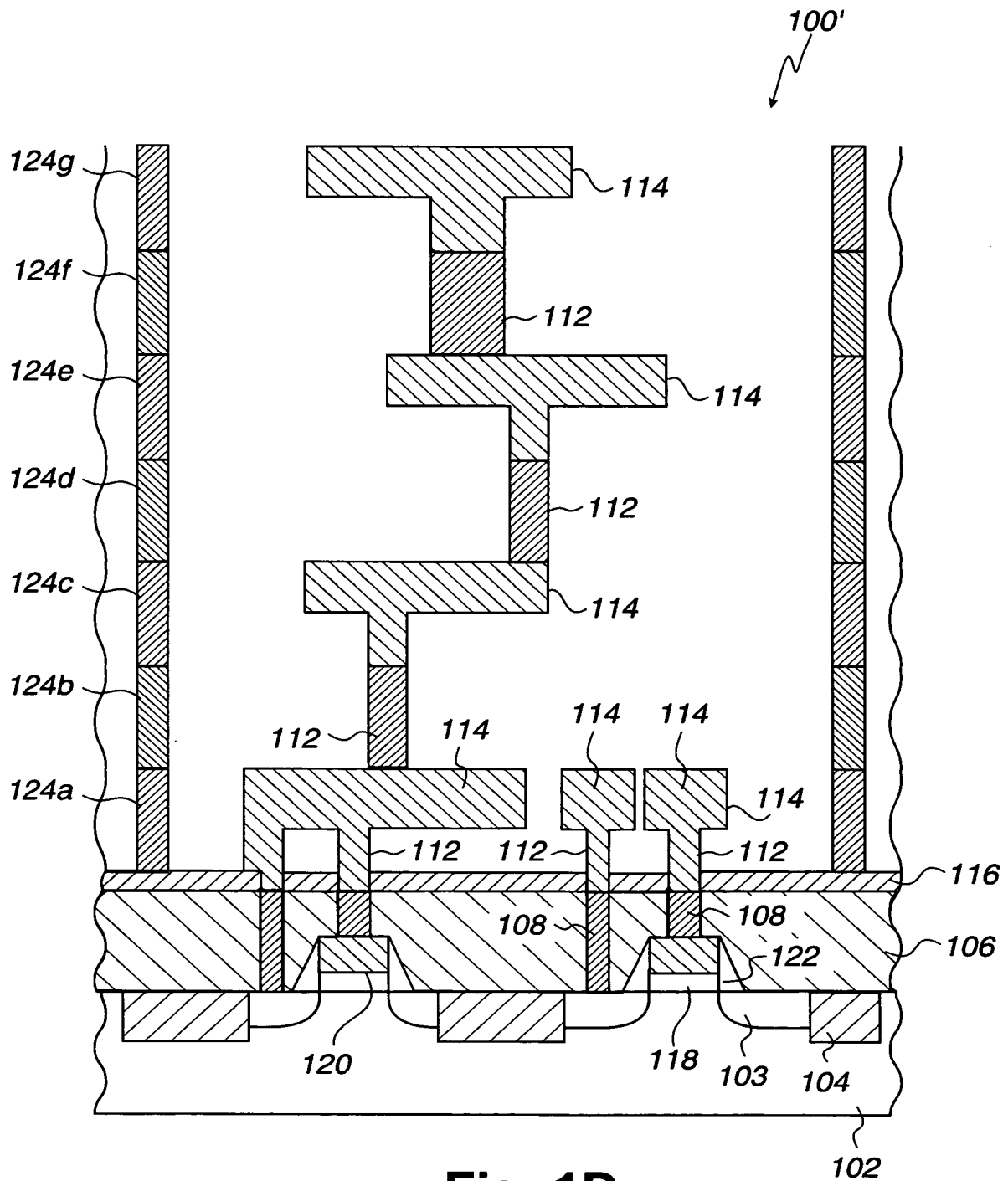


Fig. 1D

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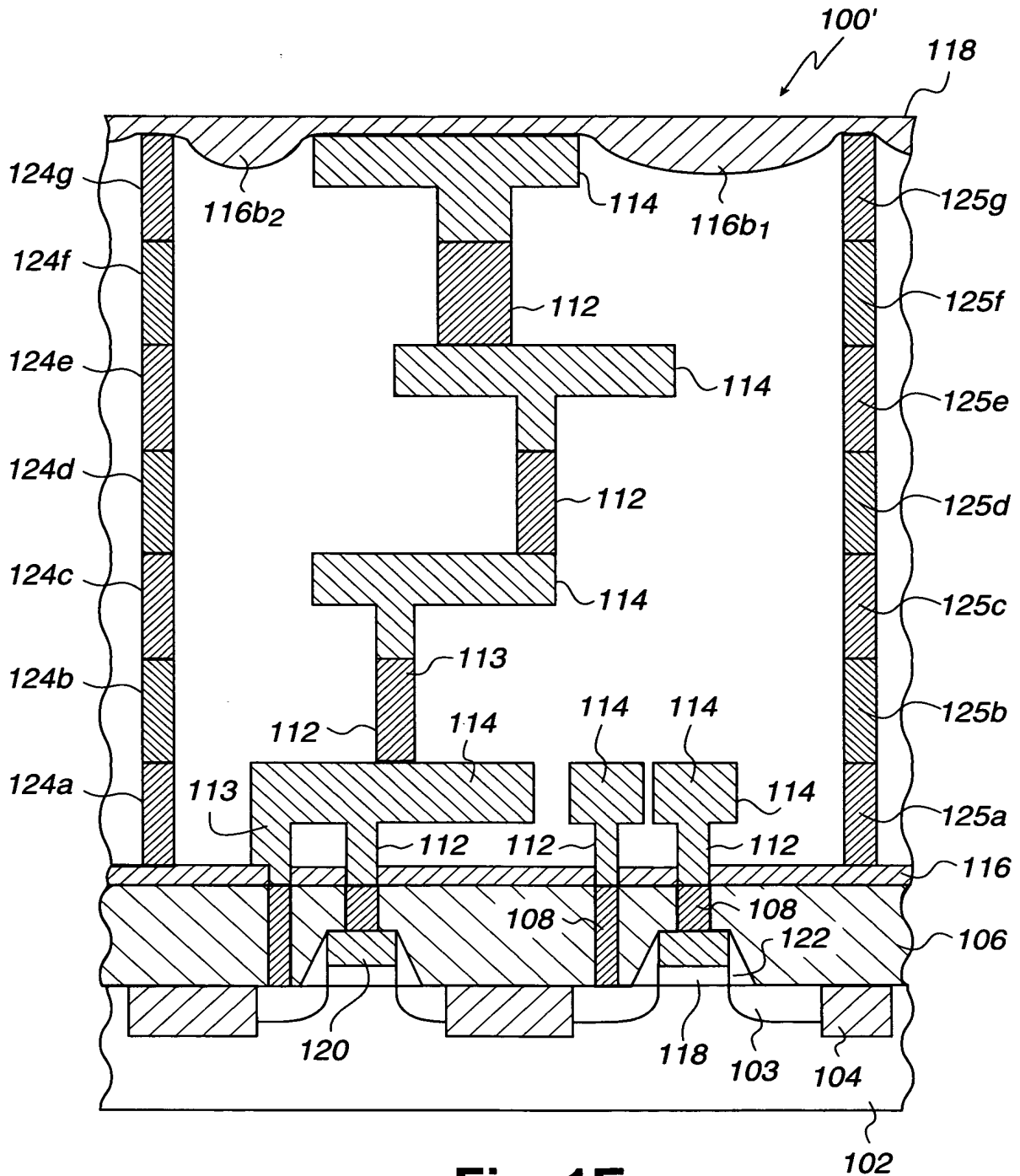


Fig. 1E

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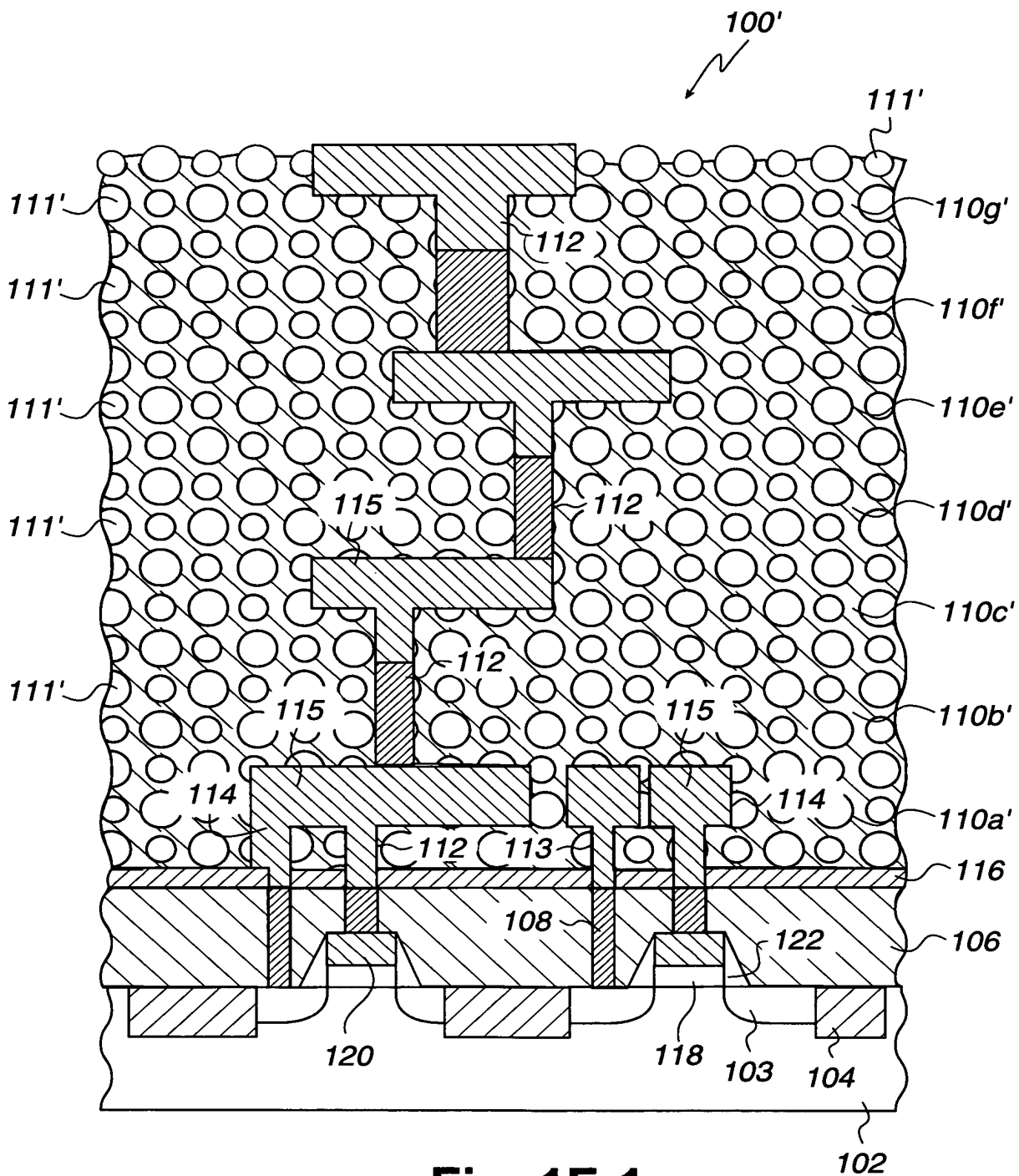
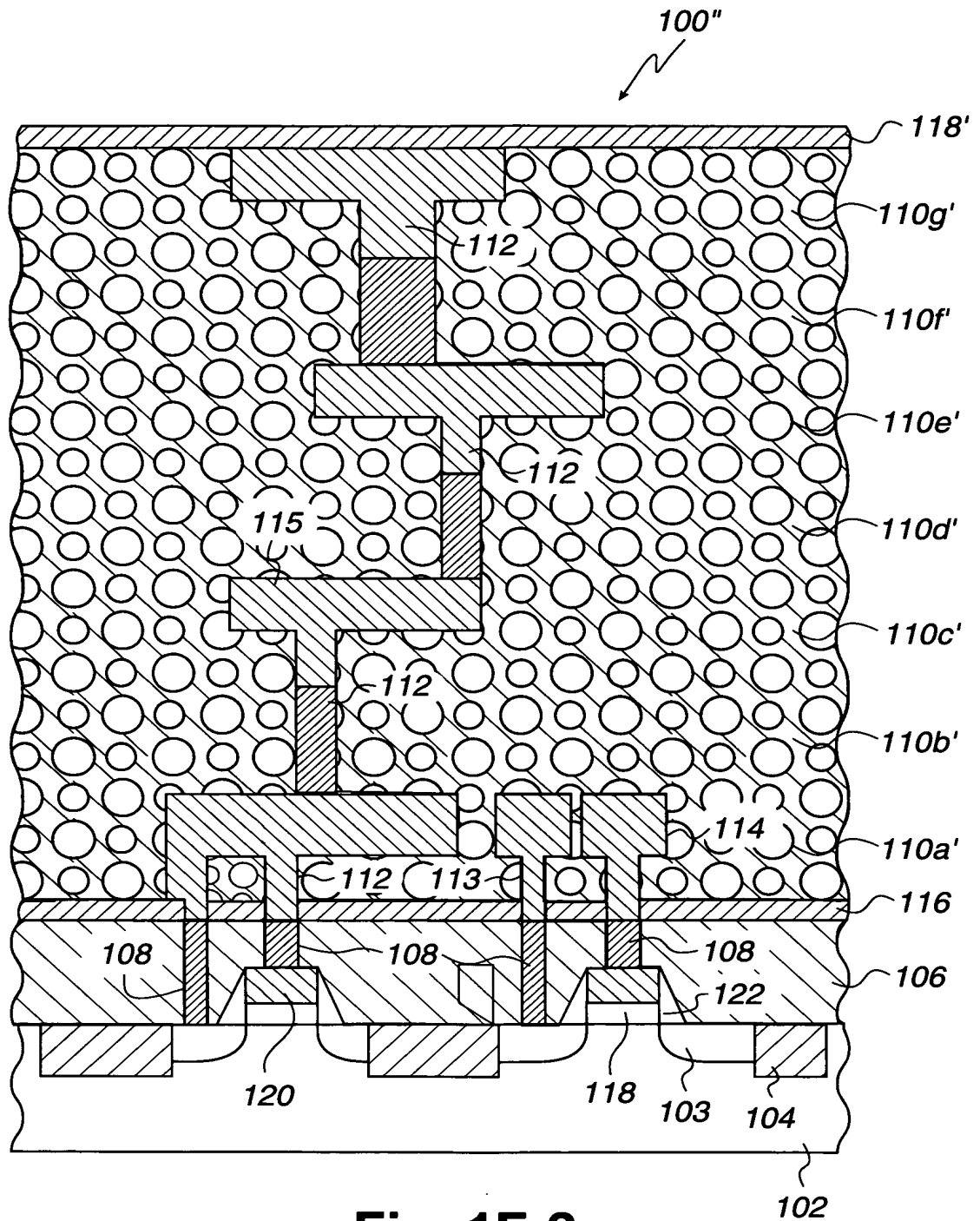


Fig. 1F-1

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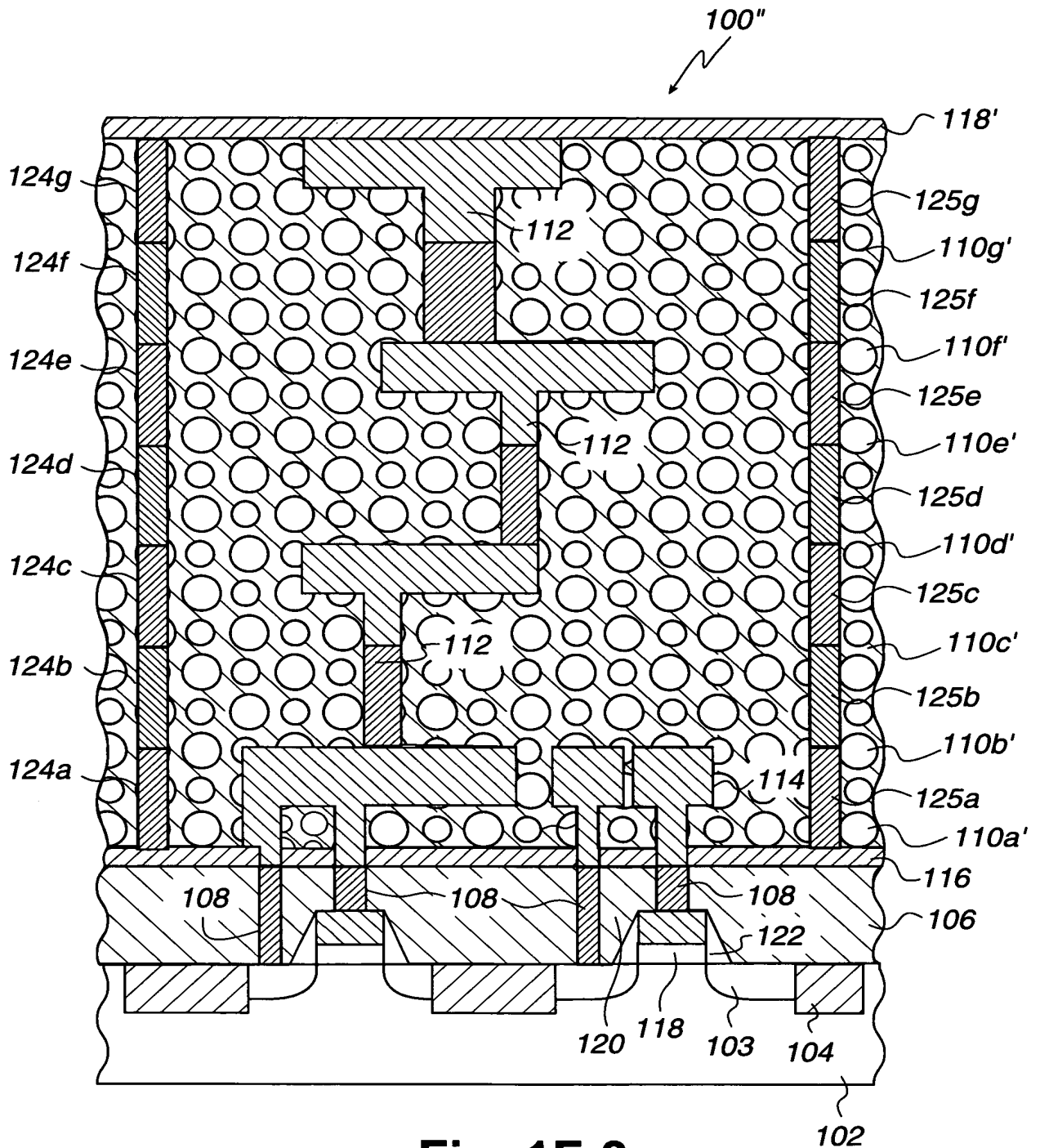
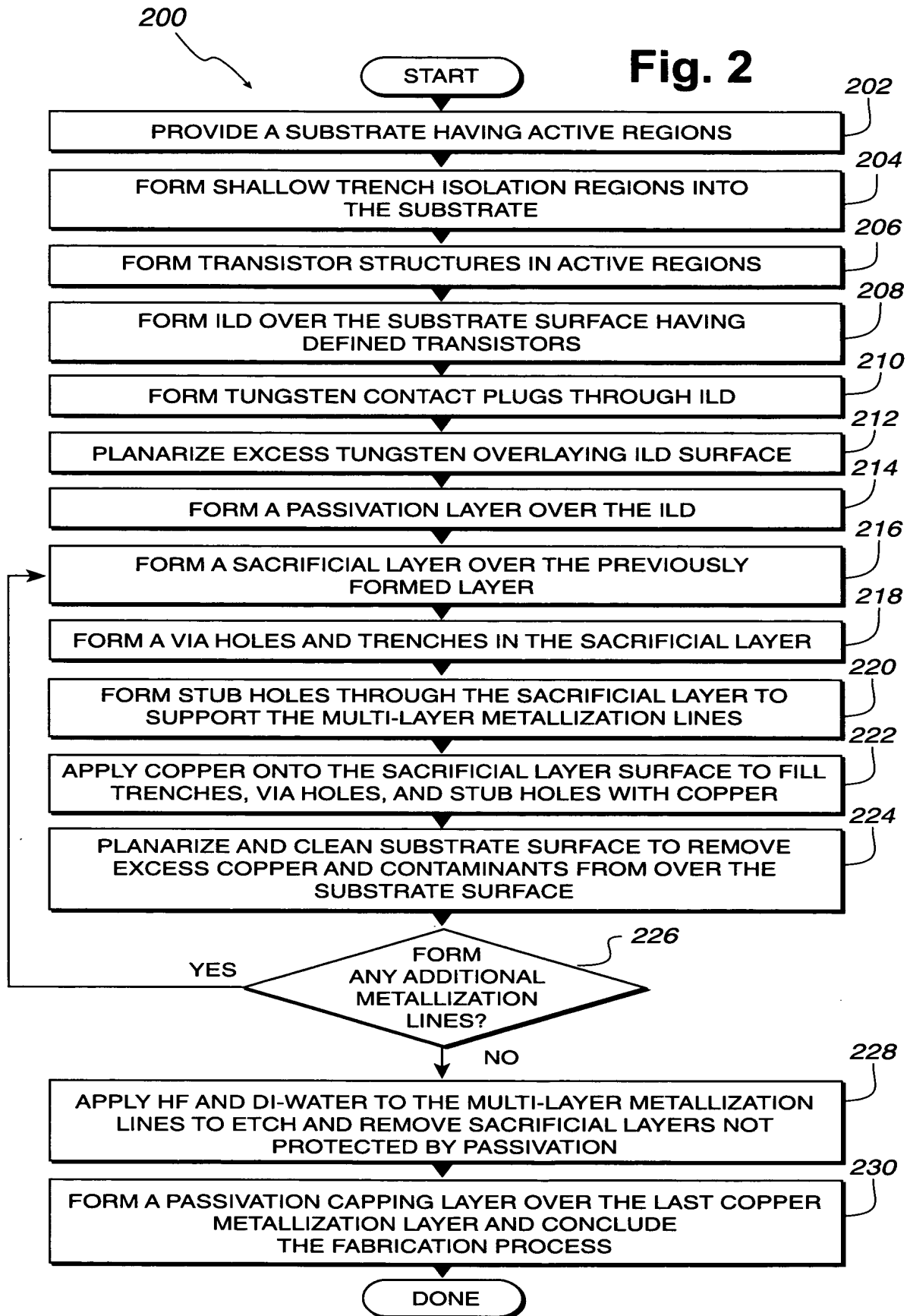


Fig. 1F-3

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Fig. 2



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Fig. 3

